

TRANSISTOR (PNP)
Plastic-Encapsulate Transistor
FEATURES

Power dissipation

$$P_{CM} : 0.2W \text{ (Tamb=25}^{\circ}\text{C)}$$

Collector current

$$I_{CM} : -0.1A$$

Collector-base Voltage

$$V_{(BR)CBO} : -60 \text{ V}$$

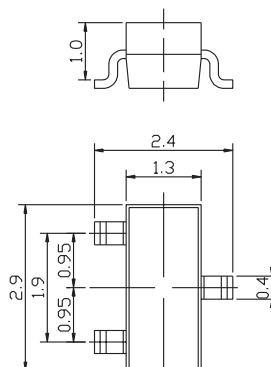
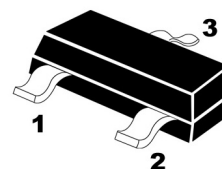
Operating and storage junction temperature range

$$T_J, T_{stg} : -55^{\circ}\text{C to } +150^{\circ}\text{C}$$

MARKING : A733LT1=CS

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR



Unit:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -5 \mu A, I_E = 0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_C = -50 \mu A, I_B = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -60V, I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0mA$		-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6V, I_C = -1mA$	120	475	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -100mA, I_B = -10mA$		-0.3	V
Transition frequency	f_r	$V_{CE} = -6V, I_C = -10mA, f = 30MHz$	100		MHz

CLASSIFICATION OF h_{FE}

Rank	L	H
Range	120-200	200-475